FAIRCHILD SEMICONDUCTOR®

May 2008

CNY171M, CNY172M, CNY173M, CNY174M, CNY17F1M, CNY17F2M, CNY17F3M, CNY17F4M, MOC8106M, MOC8107M
Phototransistor Optocouplers

Features

- UL recognized (File # E90700, Vol. 2)
- VDE recognized
  – Add option V (e.g., CNY17F2VM)
  – File #102497
- Current transfer ratio in select groups
- High BV_{CEO}: 70V minimum (CNY17XM, CNY17FXM, MOC810XM)
- Closely matched current transfer ratio (CTR) minimizes unit-to-unit variation.
- Very low coupled capacitance along with no chip to pin 6 base connection for minimum noise susceptability (CNY17FXM, MOC810XM)

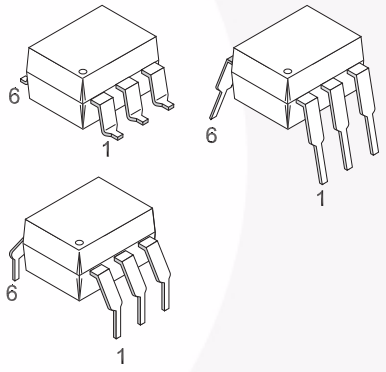
Applications

- Power supply regulators
- Digital logic inputs
- Microprocessor inputs
- Appliance sensor systems
- Industrial controls

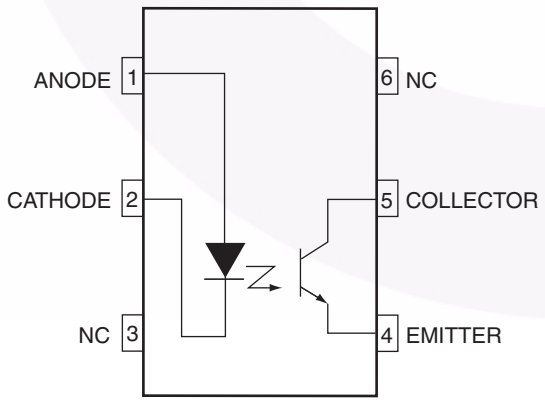
Description

The CNY17XM, CNY17FXM and MOC810XM devices consist of a Gallium Arsenide IRED coupled with an NPN phototransistor in a dual in-line package.

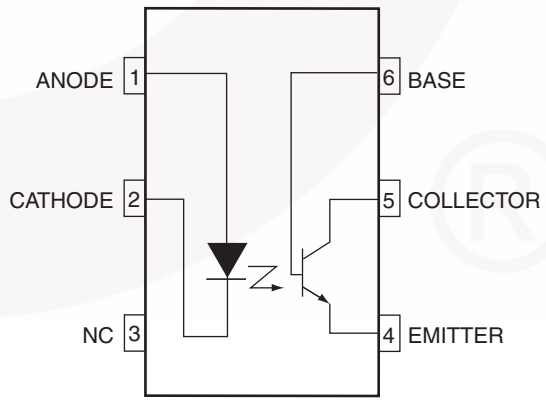
Package Outlines



Schematics



CNY17F1M/2M/3M/4M
MOC8106M/7M



CNY171M/2M/3M/4M

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameters	Value	Units
TOTAL DEVICE			
T_{STG}	Storage Temperature	-40 to +150	°C
T_{OPR}	Operating Temperature	-40 to +100	°C
T_{SOL}	Lead Solder Temperature	260 for 10 sec	°C
P_D	Total Device Power Dissipation @ 25°C (LED plus detector)	250	mW
	Derate Linearly From 25°C	2.94	mW/°C
EMITTER			
I_F	Continuous Forward Current	60	mA
V_R	Reverse Voltage	6	V
I_F (pk)	Forward Current – Peak (1µs pulse, 300pps)	1.5	A
P_D	LED Power Dissipation 25°C Ambient	120	mW
	Derate Linearly From 25°C	1.41	mW/°C
DETECTOR			
I_C	Continuous Collector Current	50	mA
V_{CEO}	Collector-Emitter Voltage	70	V
V_{ECO}	Emitter Collector Voltage	7	V
P_D	Detector Power Dissipation @ 25°C	150	mW
	Derate Linearly from 25°C	1.76	mW/°C

Electrical Characteristics (T_A = 25°C Unless otherwise specified.)[1]

Individual Component Characteristics

Symbol	Parameters	Test Conditions	Device	Min.	Typ.	Max.	Units
EMITTER							
V_F	Input Forward Voltage	I_F = 60mA	CNY17XM, CNY17FXM	1.0	1.35	1.65	V
		I_F = 10mA	MOC810XM	1.0	1.15	1.50	
C_J	Capacitance	V_F = 0 V, f = 1.0MHz	All		18		pF
I_R	Reverse Leakage Current	V_R = 6V	All		0.001	10	µA
DETECTOR							
BV_{CEO}	Breakdown Voltage Collector to Emitter	I_C = 1.0mA, I_F = 0	All	70	100		V
BV_{CBO}	Collector to Base	I_C = 10µA, I_F = 0	CNY171M/2M/3M/4M	70	120		
BV_{ECO}	Emitter to Collector	I_E = 100µA, I_F = 0	All	7	10		
I_{CEO}	Leakage Current Collector to Emitter	V_{CE} = 10 V, I_F = 0	All		1	50	nA
I_{CBO}	Collector to Base	V_{CB} = 10 V, I_F = 0	CNY171M/2M/3M/4M			20	nA
C_{CE}	Capacitance Collector to Emitter	V_{CE} = 0, f = 1MHz	All		8		pF
C_{CB}	Collector to Base	V_{CB} = 0, f = 1MHz	CNY171M/2M/3M/4M		20		pF
C_{EB}	Emitter to Base	V_{EB} = 0, f = 1MHz	CNY171M/2M/3M/4M		10		pF

Isolation Characteristics

Symbol	Characteristic	Test Conditions	Min.	Typ.*	Max.	Units
V_{ISO}	Input-Output Isolation Voltage	f = 60 Hz, t = 1 sec., $I_{I-O} \le 2\mu A$[4]	7500			Vac(pk)
R_{ISO}	Isolation Resistance	V_{I-O} = 500 VDC[4]	10^{11}			Ω
C_{ISO}	Isolation Capacitance	V_{I-O} = Ø, f = 1MHz[4]		0.2		pF

Transfer Characteristics (T_A = 25°C Unless otherwise specified.)[3]

Symbol	DC Characteristics		Test Conditions	Min.	Typ.*	Max.	Units
COUPLED							
(CTR)[2]	Output Collector Current	MOC8106M	I_F = 10mA, V_{CE} = 10V	50		150	%
		MOC8107M		100		300	
		CNY17F1M	I_F = 10mA, V_{CE} = 5V	40		80	
		CNY17F2M		63		125	
		CNY17F3M		100		200	
		CNY17F4M		160		320	
		CNY171M		40		80	
		CNY172M		63		125	
		CNY173M		100		200	
		CNY174M		160		320	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	CNY17XM/FXM	I_C = 2.5mA, I_F = 10mA			0.4	V
		MOC8106M/7M	I_C = 500µA, I_F = 5.0mA				

*All typicals at T_A = 25°C

Electrical Characteristics (Continued) (T_A = 25°C Unless otherwise specified.)[1]

Transfer Characteristics (Continued)[3]

Symbol	AC Characteristics[4]		Test Conditions	Min.	Typ.*	Max.	Units
NON-SATURATED SWITCHING TIME							
t_{on}	Turn-On Time	All Devices	I_C = 2.0mA, V_{CC} = 10V, R_L = 100Ω		2	10	µs
t_{off}	Turn-Off Time	All Devices	I_C = 2.0mA, V_{CC} = 10V, R_L = 100Ω		3	10	µs
t_d	Delay Time	CNY17XM/XFM	I_F = 10mA, V_{CC} = 5V, R_L = 75Ω			5.6	µs
t_r	Rise Time	All Devices	I_C = 2.0mA, V_{CC} = 10V, R_L = 100Ω		1		µs
		CNY17XM/FXM	I_F = 10mA, V_{CC} = 5V, R_L = 75Ω			4.0	
t_s	Storage Time	CNY17XM/FXM	I_F = 10mA, V_{CC} = 5V, R_L = 75Ω			4.1	µs
t_f	Fall Time	All Devices	I_C = 2.0mA, V_{CC} = 10V, R_L = 100Ω		2		µs
		CNY17XM/FXM	I_F = 10mA, V_{CC} = 5V, R_L = 75Ω			3.5	
SATURATED SWITCHING TIMES							
t_{on}	Turn-on Time	CNY171M/F1M	I_F = 20mA, V_{CC} = 5V, R_L = 1kΩ			5.5	µs
		CNY172M/3M/4M CNY17F2M/F3M/F4M	I_F = 10mA, V_{CC} = 5V, R_L = 1kΩ			8.0	
t_r	Rise Time	CNY171M/F1M	I_F = 20mA, V_{CC} = 5V, R_L = 1kΩ			4.0	µs
		CNY172M/3M/4M CNY17F2M/F3M/F4M	I_F = 10mA, V_{CC} = 5V, R_L = 1kΩ			6.0	
t_d	Delay Time	CNY171M/F1M	I_F = 20mA, V_{CC} = 5V, R_L = 1kΩ			5.5	µs
		CNY172M/3M/4M CNY17F2M/F3M/F4M	I_F = 10mA, V_{CC} = 5V, R_L = 1kΩ			8.0	
t_{off}	Turn-off Time	CNY171M/F1M	I_F = 20mA, V_{CE} = 0.4V			34	µs
		CNY172M/3M/4M CNY17F2M/F3M/F4M	I_F = 10mA, V_{CE} = 0.4V			39	
t_f	Fall Time	CNY171M/F1M	I_F = 20mA, V_{CC} = 5V, R_L = 1kΩ			20.0	µs
		CNY172M/3M/4M CNY17F2M/F3M/F4M	I_F = 10mA, V_{CC} = 5V, R_L = 1kΩ			24.0	
t_s	Storage Time	CNY171M/F1M	I_F = 20mA, V_{CC} = 5V, R_L = 1kΩ			34.0	µs
		CNY172M/3M/4M CNY17F2M/F3M/F4M	I_F = 10mA, V_{CC} = 5V, R_L = 1kΩ			39.0	

*All typicals at T_A = 25°C

Notes:

1. Always design to the specified minimum/maximum electrical limits (where applicable).
2. Current Transfer Ratio (CTR) = I_C/I_F x 100%.
3. For test circuit setup and waveforms, refer to Figures 10 and 11.
4. For this test, Pins 1 and 2 are common, and Pins 4 are 5 are common.

Typical Performance Characteristics

Fig. 1 Normalized CTR vs. Forward Current

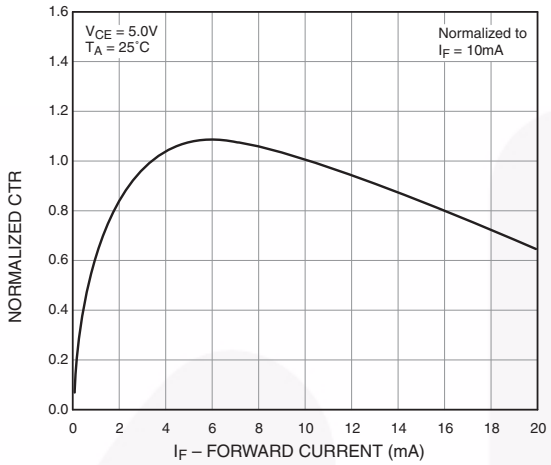


Fig. 2 Normalized CTR vs. Ambient Temperature

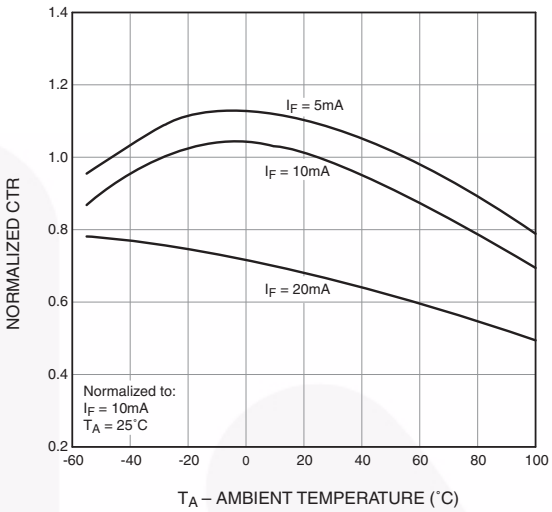


Fig. 3 CTR vs. RBE (Unsaturated)

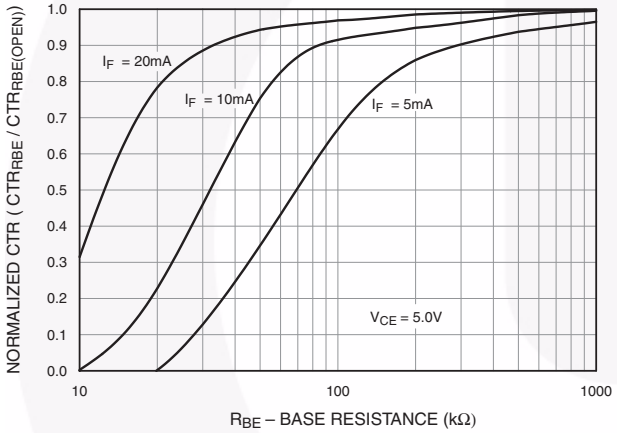


Fig. 4 CTR vs. RBE (Saturated)

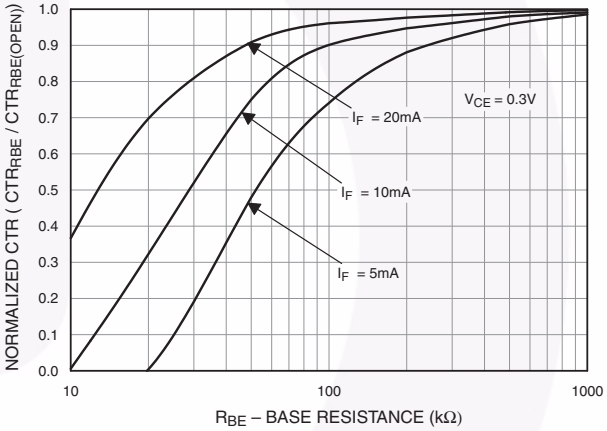


Fig. 5 Switching Speed vs. Load Resistor

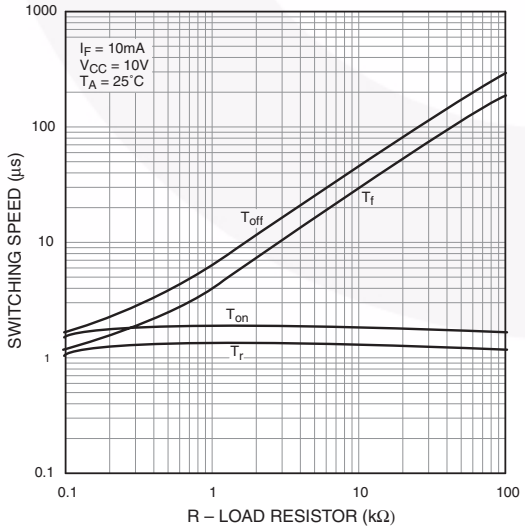
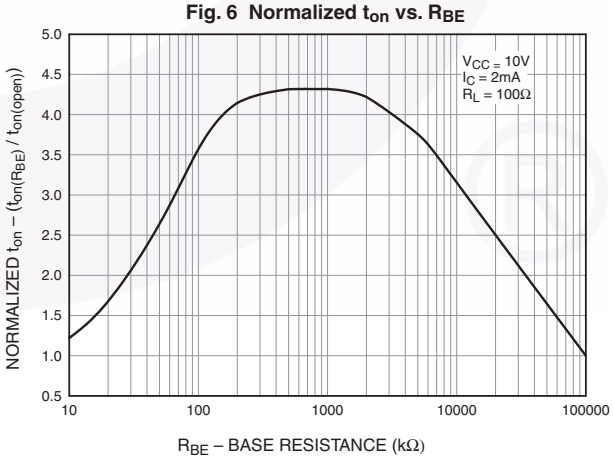


Fig. 6 Normalized t_{on} vs. R_{BE}



Typical Performance Characteristics (Continued)

Fig. 7 Normalized t_{off} vs. R_{BE}

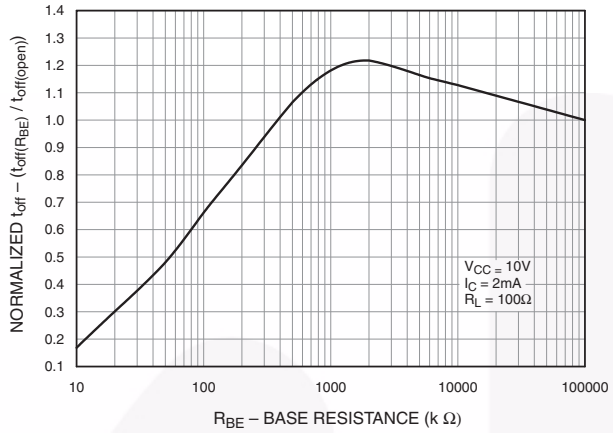


Fig. 8 LED Forward Voltage vs. Forward Current

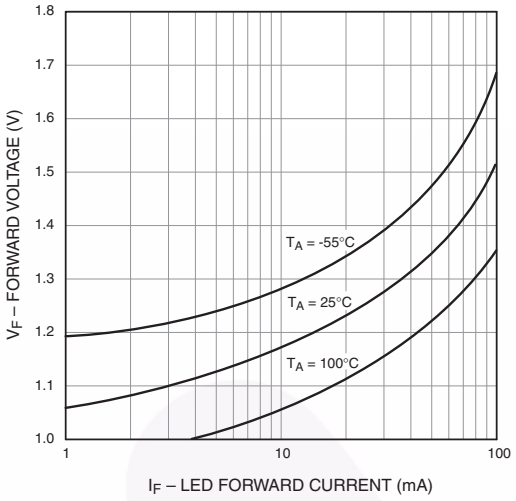
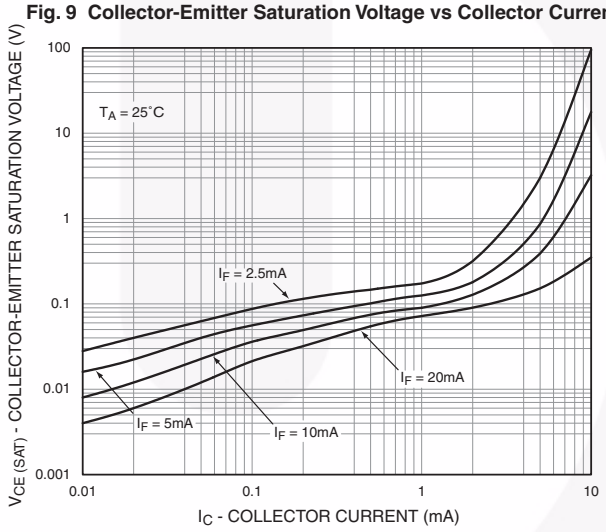


Fig. 9 Collector-Emitter Saturation Voltage vs Collector Current



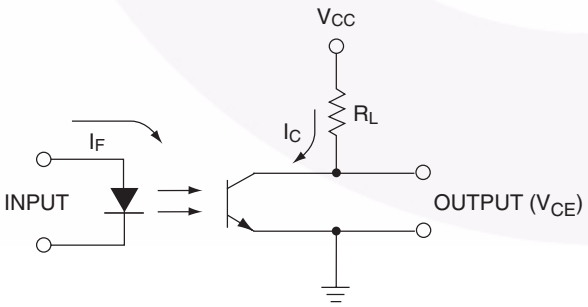


Figure 10. Switching Time Test Circuit

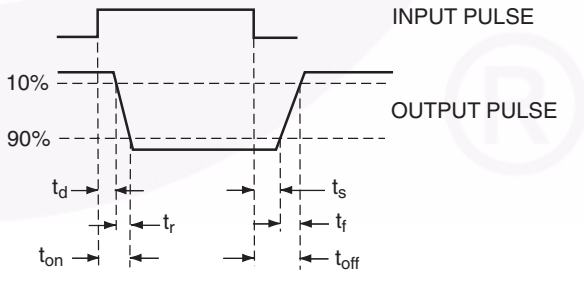
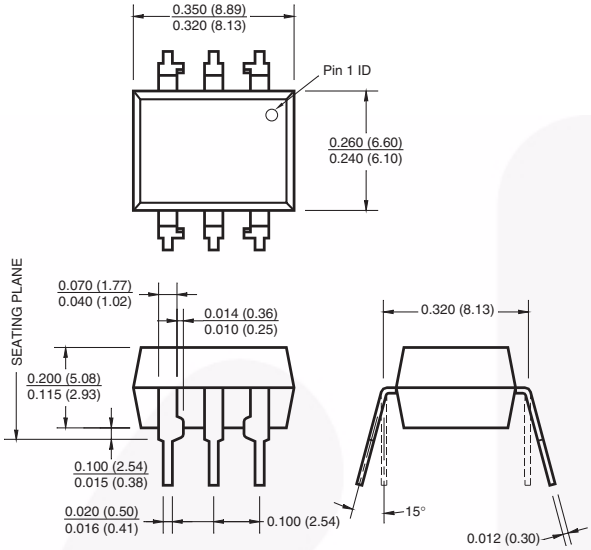


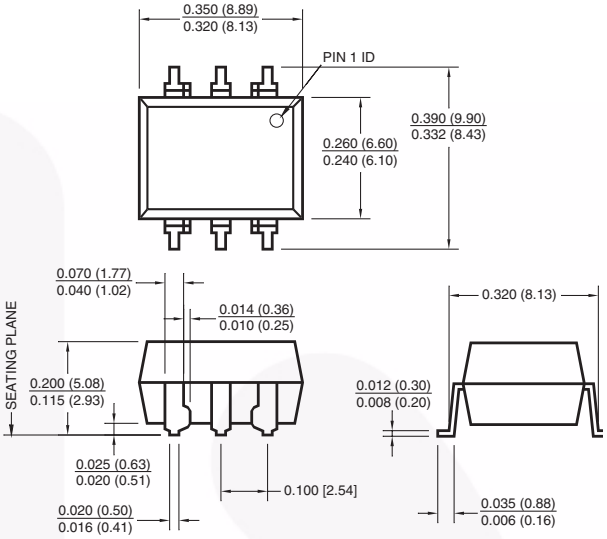
Figure 11. Switching Time Waveforms

Package Dimensions

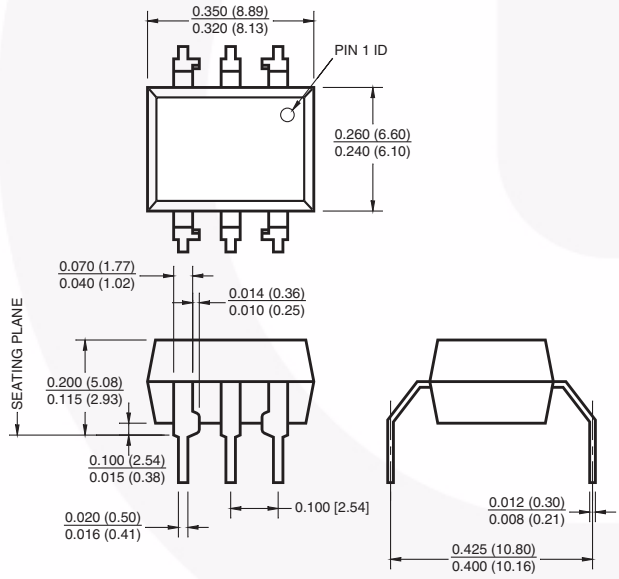
Through Hole



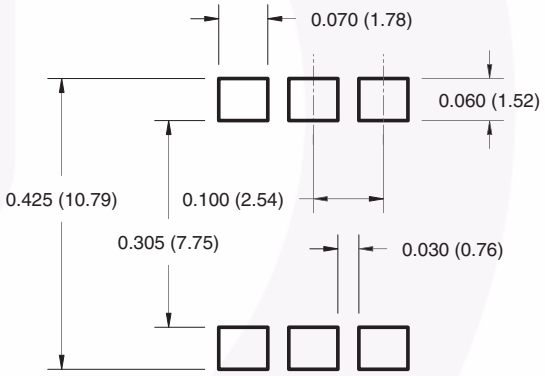
Surface Mount



0.4" Lead Spacing



Recommended Pad Layout for Surface Mount Leadform

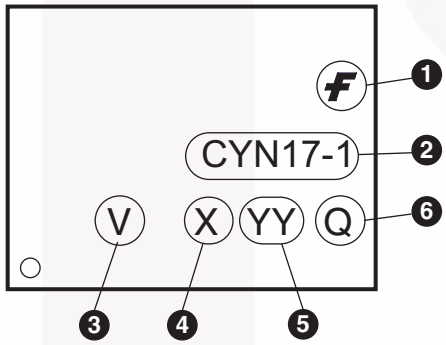


Note:
All dimensions are in inches (millimeters)

Ordering Information

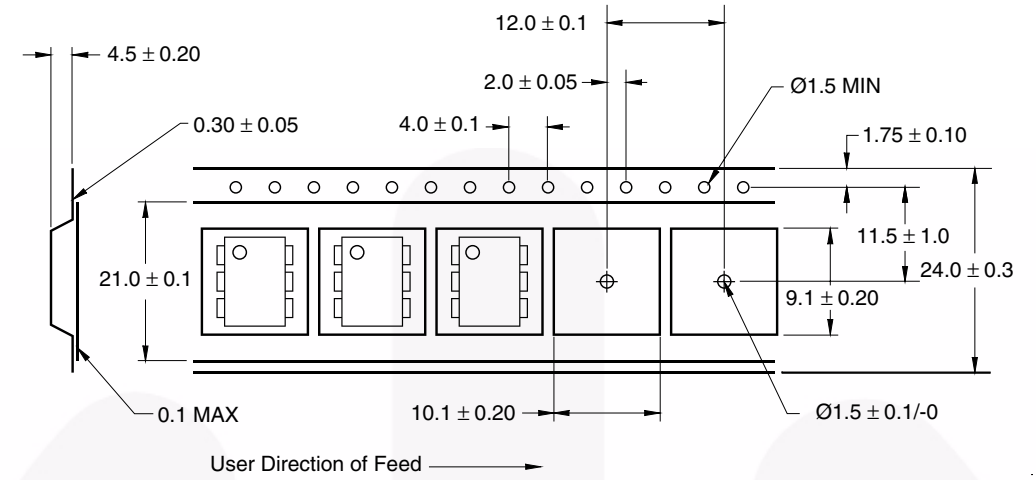
Option	Order Entry Identifier (Example)	Description
No option	CYN171M	Standard Through Hole Device
S	CYN171SM	Surface Mount Lead Bend
SR2	CYN171SR2M	Surface Mount; Tape and Reel
T	CYN171TM	0.4" Lead Spacing
V	CYN171VM	VDE 0884
TV	CYN171TVM	VDE 0884, 0.4" Lead Spacing
SV	CYN171SVM	VDE 0884, Surface Mount
SR2V	CYN171SR2VM	VDE 0884, Surface Mount, Tape and Reel

Marking Information

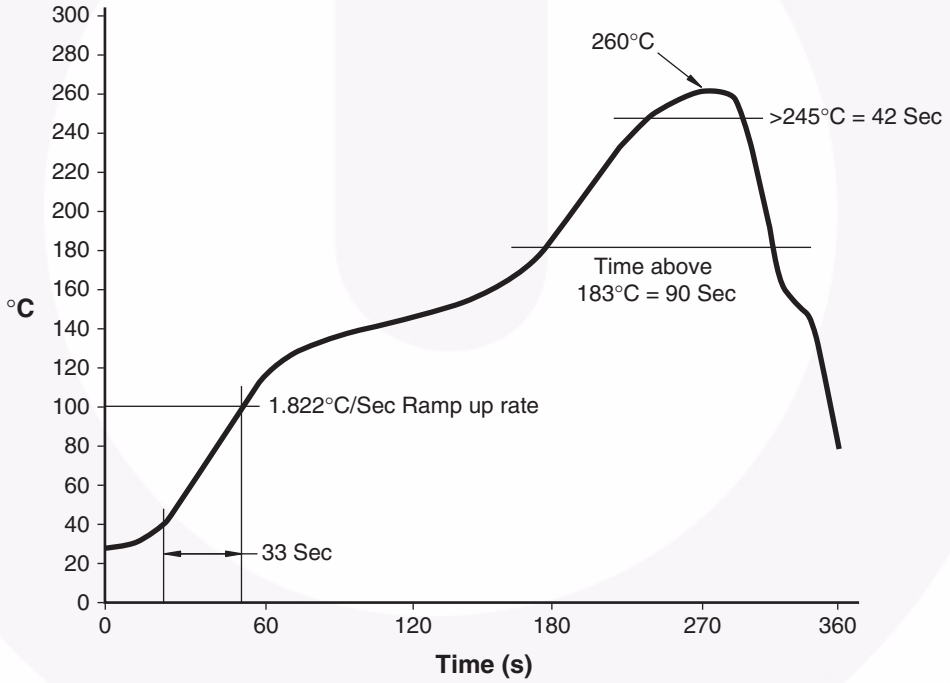


Definitions	
1	Fairchild logo
2	Device number
3	VDE mark (Note: Only appears on parts ordered with VDE option – See order entry table)
4	One digit year code, e.g., ‘7’
5	Two digit work week ranging from ‘01’ to ‘53’
6	Assembly package code

Carrier Tape Specification



Reflow Profile



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2. A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	This datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

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